WSD20L75DN

P-Ch MOSFET

General Description

Description The WSD20L75DN uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

Product Summery

BV_{DSS}	R_{DSON}	I_D
-20V	4.8mΩ	-75A

Features

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Applications

- Load switch
- Battery protection

DFN3X3-8 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-75	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-55	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-13	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-10	A
I_{DM}	Pulsed Drain Current[2]	-200	A
EAS	Single Pulse Avalanche Energy[3]	125	mJ
I_{AS}	Avalanche Current	-50	A
P_D@T_C=25℃	Total Power Dissipation[4]	83	W
P_D@T_A=25℃	Total Power Dissipation[4]	6.2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	55	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	20	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.5	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0232	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V , I_D=-20A	---	4.8	6.0	mΩ
		V_{GS}=-2.5V , I_D=-20A	---	6.2	8	
		V_{GS}=-1.8V , I_D=-10A	---	8.0	10	
		V_{GS}=-1.5V , I_D=-8A	---	12	15.5	
		V_{GS}=-1.2V , I_D=-5A	---	17.6	19.5	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.4	-0.6	-1.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-20V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±8V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-20A	---	80	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	3	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-20A	---	55	75	nC
Q_{gs}	Gate-Source Charge		---	10	---	
Q_{gd}	Gate-Drain Charge		---	15	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3Ω I_D=-20A ,R_L=0.5Ω	---	18	---	ns
T_r	Rise Time		---	42	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time		---	23	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	577	---	
C_{rss}	Reverse Transfer Capacitance		---	445	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=-10V , L=0.5mH , I_{AS}=-10A	100	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-45	A
I_{SM}	Pulsed Source Current[2,6]		---	---	-90	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-10A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-10A,dI/dt=100A/μs, T_J=25℃	---	47	---	nS
Q_{rr}	Reverse Recovery Charge		---	53	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t≦10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-10V,V_{GS}=-10V,L=0.1mH,I_{AS}=-10A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

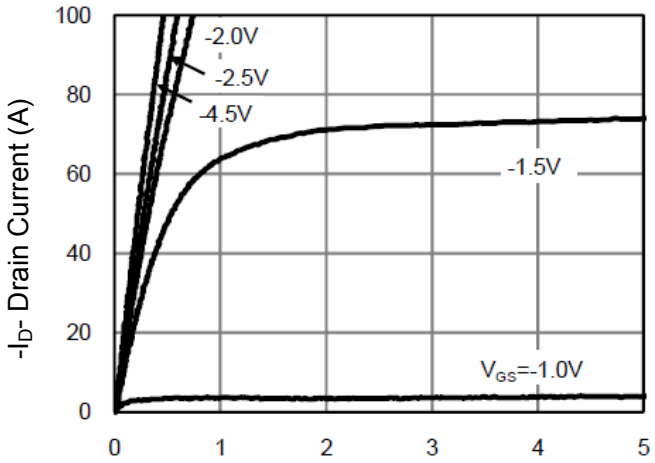

Figure 1 Output Characteristics

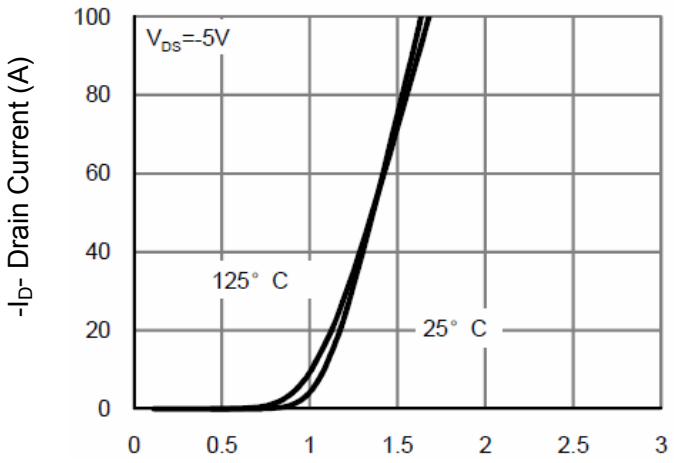

Figure 2 Transfer Characteristics

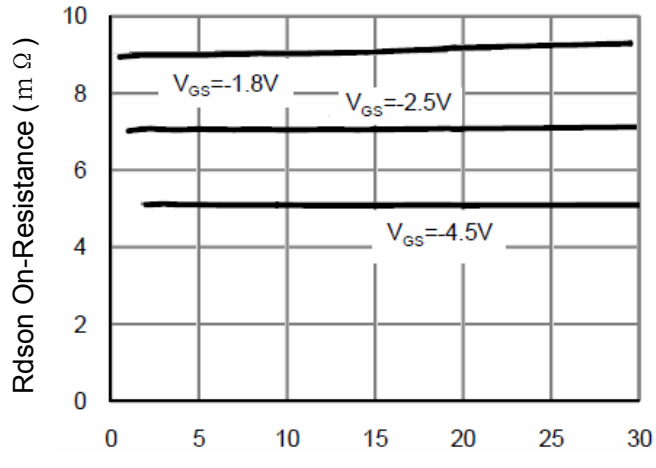

Figure 3 Rdson- Drain Current

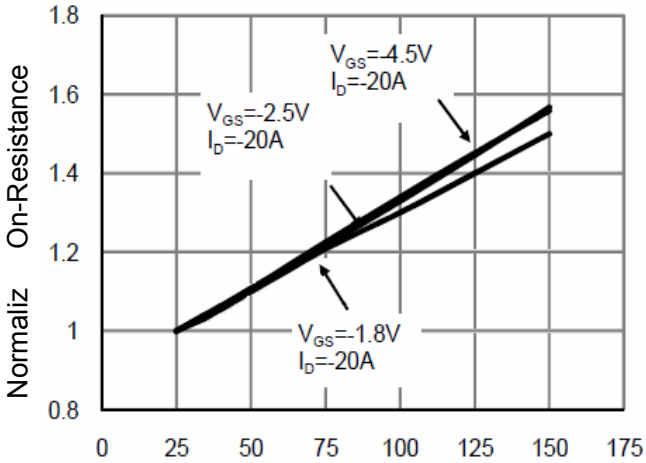

Figure 4 Rdson-Junction Temperature

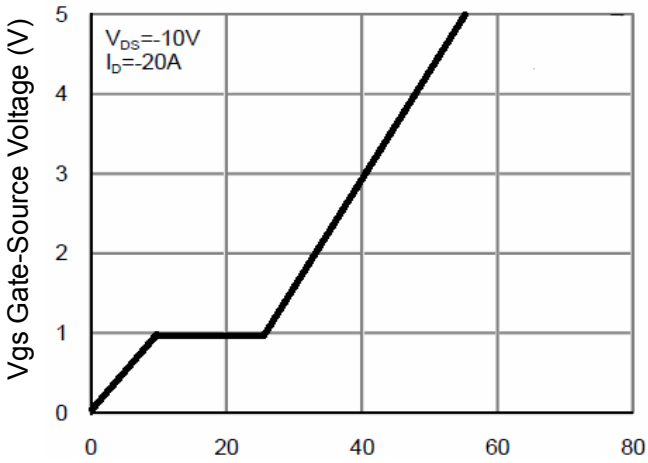

Figure 5 Gate Charge

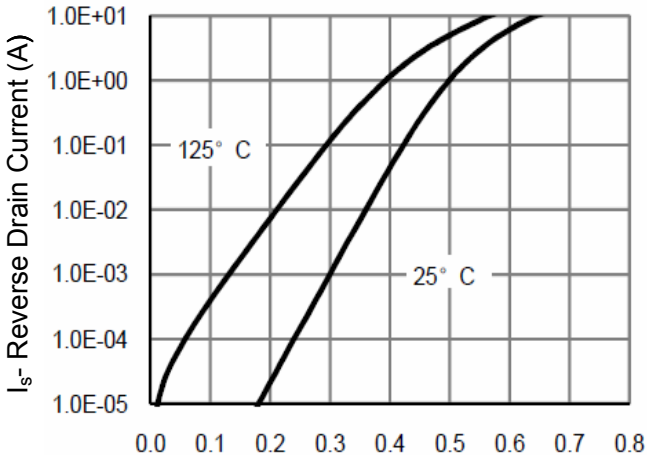

Figure 6 Source- Drain Diode Forward

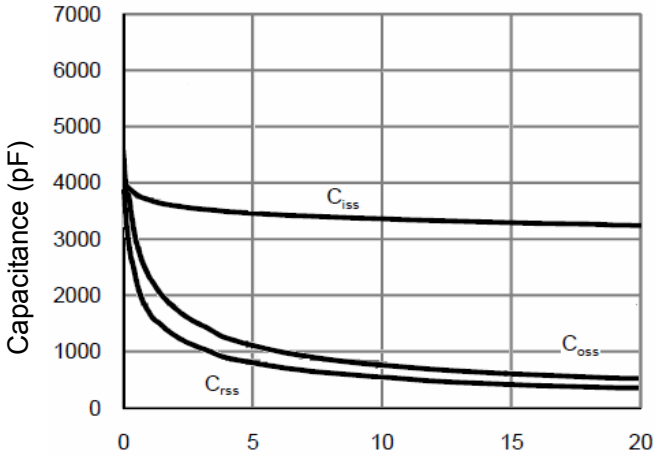

Figure 7 Capacitance vs Vds

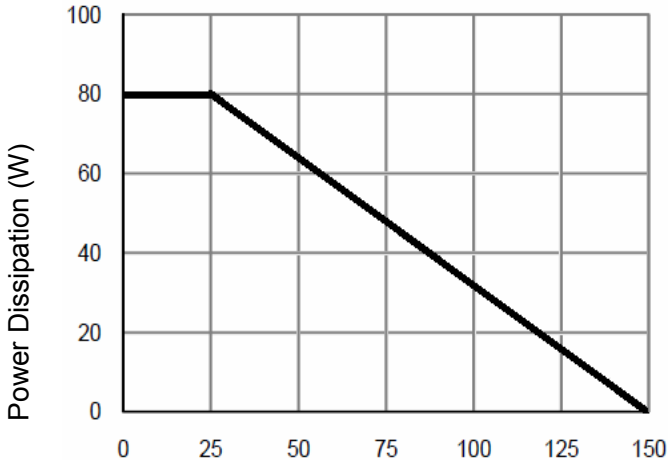

Figure 9 Power De-rating

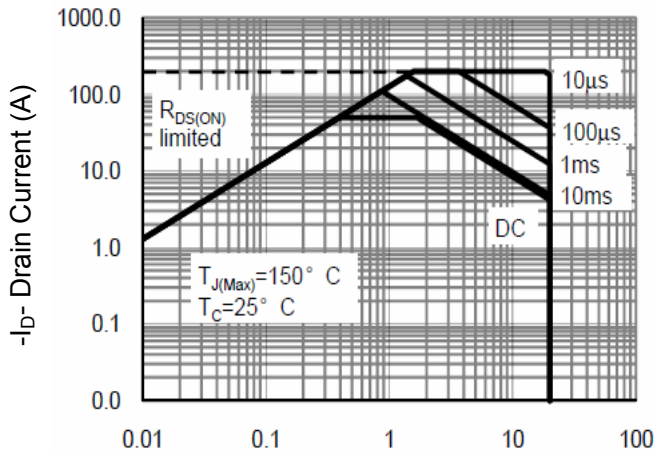

Figure 8 Safe Operation Area

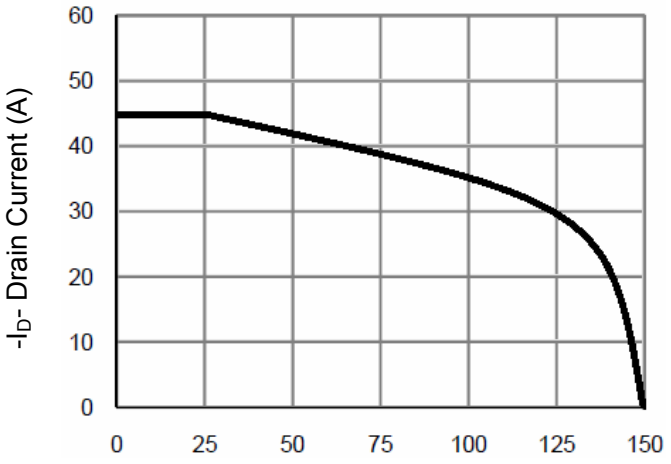

Figure 10 -Current De-rating

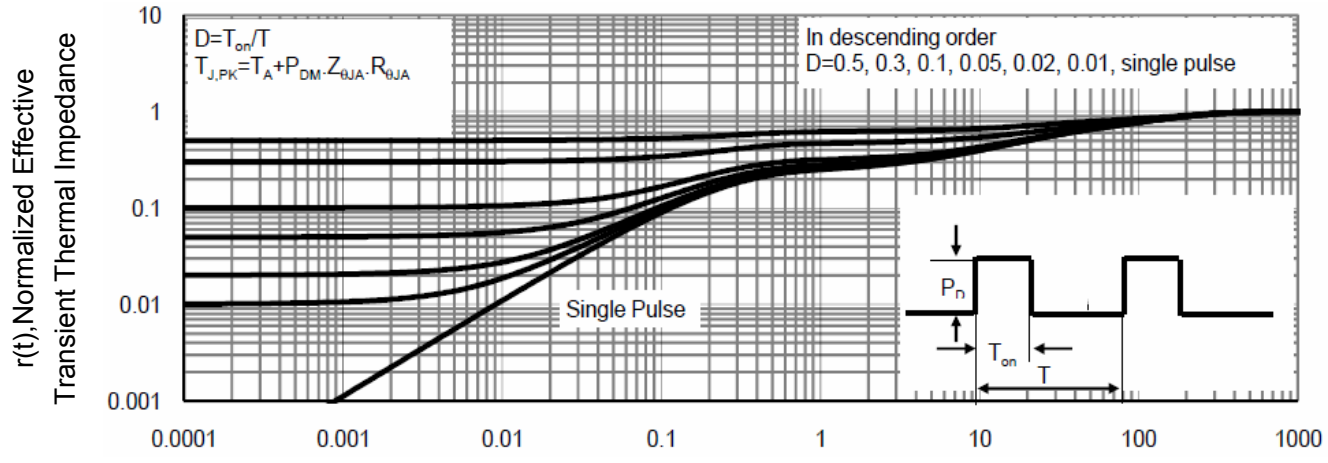

Figure 11 Normalized Maximum Transient Thermal Impedance

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